

ENERGY GAP OF SEMICONDUCTOR USING SILICON DIODE

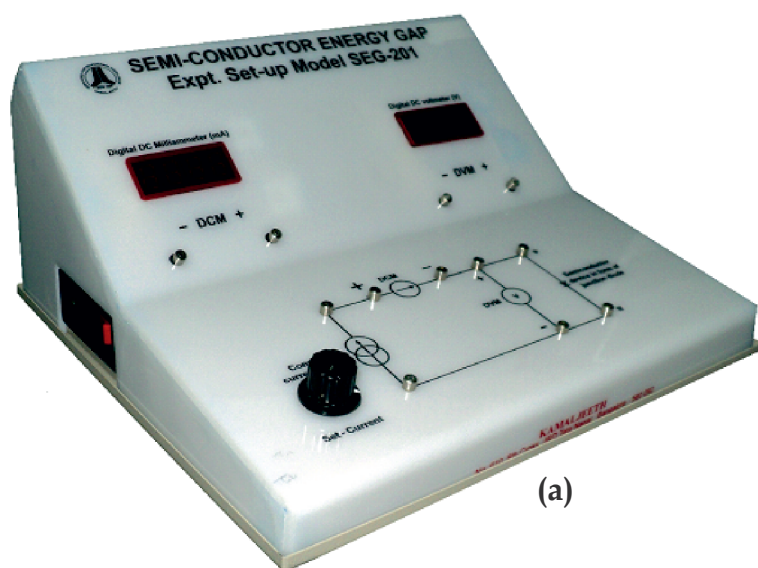
Model: SEG-201/109

Experiment(s):

1. Determination of Energy gap of a semiconductor sample

(For more details, procedure & manual visit: www.kamaljeeth.net)

Reference : Lab Experiments Journal vol-5, No.1, Page-11



(a)



(b)



(c)

Experiment setup consists:

- Semiconductor energy gap kit
- Digital thermostat
- Electric kettle & stand

Specifications:

a) Semiconductor energy gap kit

Voltmeter: 0-20 V
Resolution: 0.01 V
Ammeter: 0-200 mA
Resolution: 0.1 mA
Source: Built-in constant current source with variable output current setting
Rated Input: 220 V/50 Hz
or 110 V/60 Hz
Power consumption: <40 W
Cabinet: Acrylic body, aluminium bottom
Connectors:
2 mm - 2 mm brass moulded patch cords

b) Digital thermometer

Range: 300 °C
Resolution: 0.1 °C

c) Electric kettle & stand

Kettle capacity: 0.5 L
Maximum temperature: 100 °C
Stand: Height adjustable and holds test tube with sample and temperature probe



KAMALJEETH INSTRUMENTS

ESTD. 1990

Address: No. 610, 5th main, 8th cross Tatanagar, Bangalore - 560092, INDIA

Website: www.kamaljeeth.net, Email: labexperiments@kamaljeeth.net

3 years manufacturing warranty